Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 × 0.62 × 0.37 mm

3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-530	mA
Static charac	cteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -500 mA; T_j = 25 °C		-	1	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0606-3 (SOT8001)	G S 017aaa259

6. Ordering information

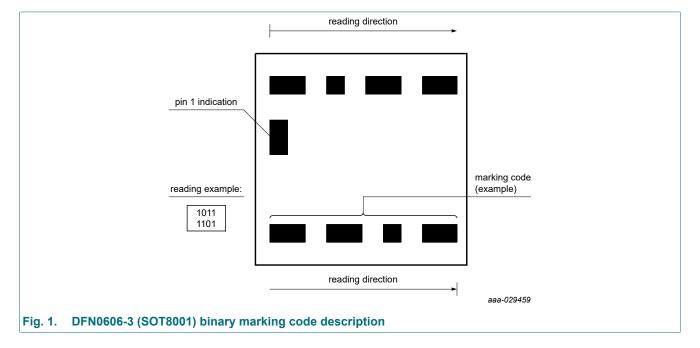
Table 3. Ordering information

<u></u>						
Type number	Package					
	Name	Description	Version			
PMH950UPE	DFN0606-3	plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm	SOT8001			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMH950UPE	0001 0100



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-530	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-360	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	370	mW
			[1]	-	625	mW
		T _{sp} = 25 °C		-	2.2	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode			1		
Is	source current	T _{amb} = 25 °C	[1]	-	-530	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

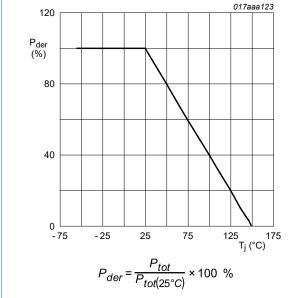


Fig. 2. Normalized total power dissipation as a function of junction temperature

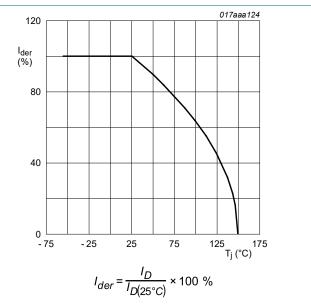


Fig. 3. Normalized continuous drain current as a function of junction temperature

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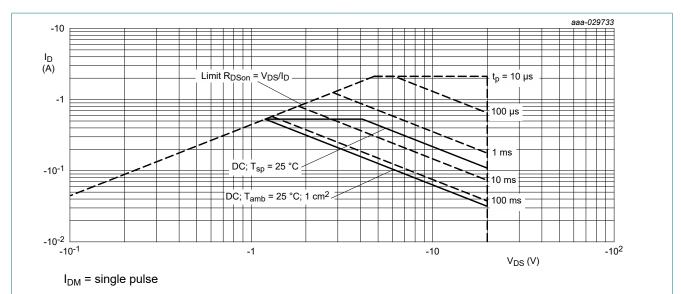


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	300	340	K/W
junction	junction to ambient	ction to ambient	[2]	-	175	200	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	50	58	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

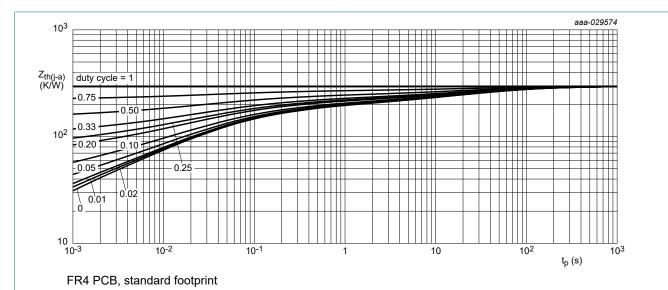


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

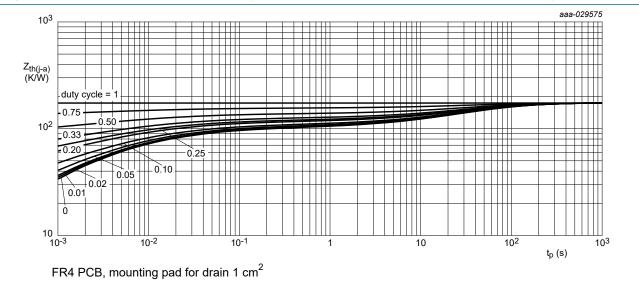


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

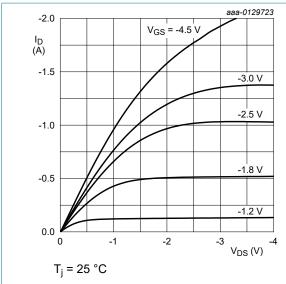
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10. Characteristics

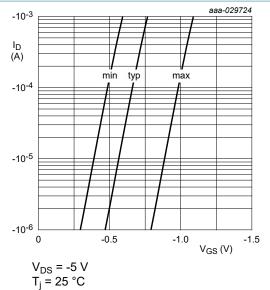
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source or resistance	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -500 \text{ mA}; T_j = 25 \text{ °C}$	-	1	1.4	Ω
	resistance	V _{GS} = -4.5 V; I _D = -500 mA; T _j = 150 °C	-	1.6	2.3	Ω
		V_{GS} = -2.5 V; I_D = -200 mA; T_j = 25 °C	-	1.4	2.2	Ω
		V _{GS} = -1.8 V; I _D = -40 mA; T _j = 25 °C	-	1.8	3.3	Ω
		V_{GS} = -1.5 V; I_D = -40 mA; T_j = 25 °C	-	2.1	5.5	Ω
		V_{GS} = -1.2 V; I_D = -10 mA; T_j = 25 °C	-	2.9	-	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -600 mA; T_{j} = 25 °C	-	700	-	mS
R _G	gate resistance	f = 1 MHz	-	3.7	-	Ω
Dynamic ch	naracteristics		,			
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -600 mA; V _{GS} = -4 V;	-	0.29	0.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.08	-	nC
Q_{GD}	gate-drain charge		-	0.08	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	36	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	6.3	-	pF
C _{rss}	reverse transfer capacitance		-	4.7	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -10 V; I _D = -600 mA; V _{GS} = -4 V;	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
$t_{d(off)}$	turn-off delay time		-	4	-	ns
t _f	fall time		-	6	-	ns
Source-dra	in diode		l			
V_{SD}	source-drain voltage	I _S = -600 mA; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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Output characteristics: drain current as a Fig. 7. function of drain-source voltage; typical values | Fig. 8.



Sub-threshold drain current as a function of gate-source voltage

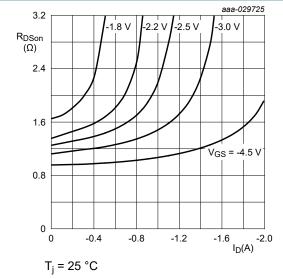


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

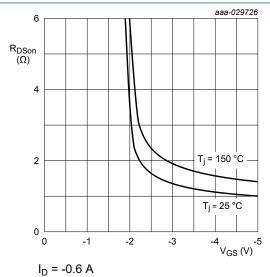


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, P-channel Trench MOSFET

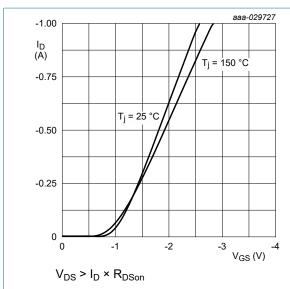


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

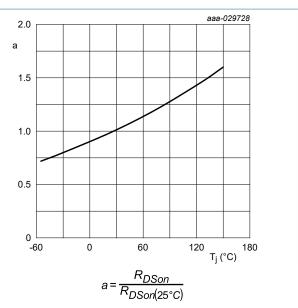


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

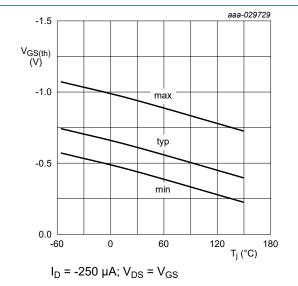
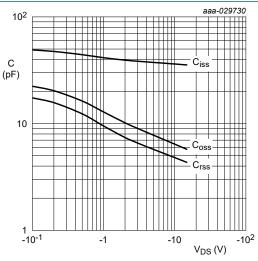


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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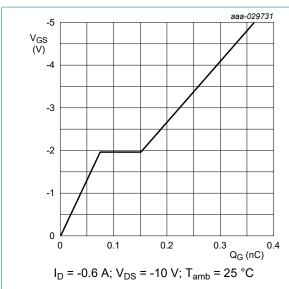


Fig. 15. Gate-source voltage as a function of gate charge; typical values

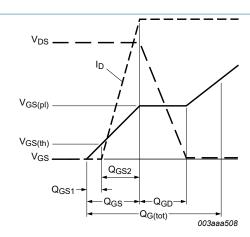


Fig. 16. Gate charge waveform definitions

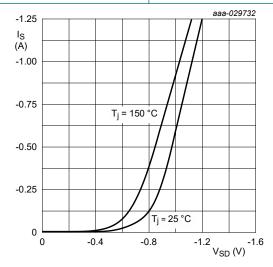
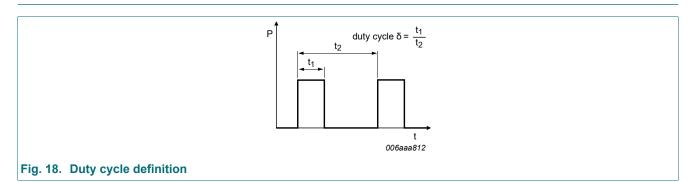


Fig. 17. Source current as a function of source-drain voltage; typical values

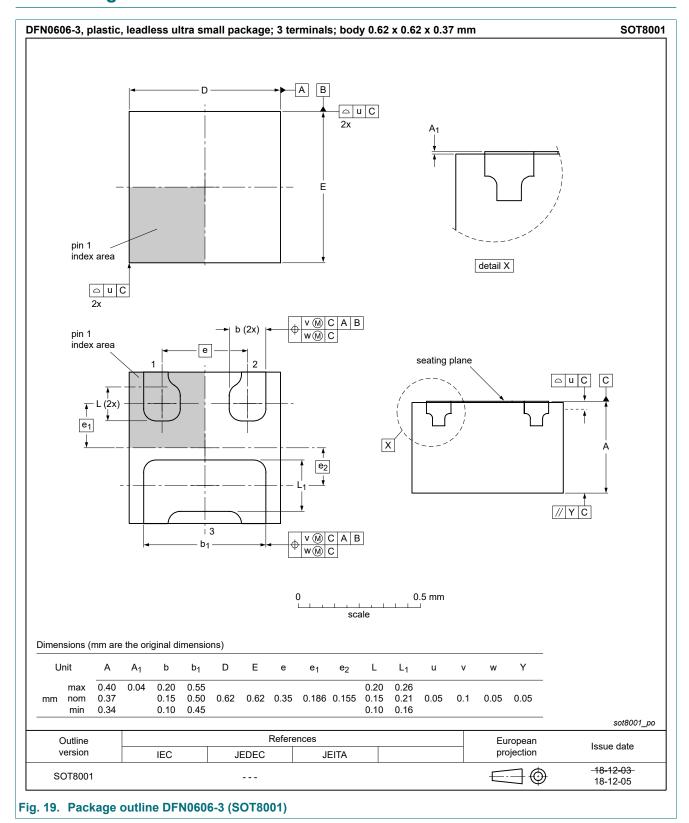
11. Test information

 $V_{GS} = 0 V$



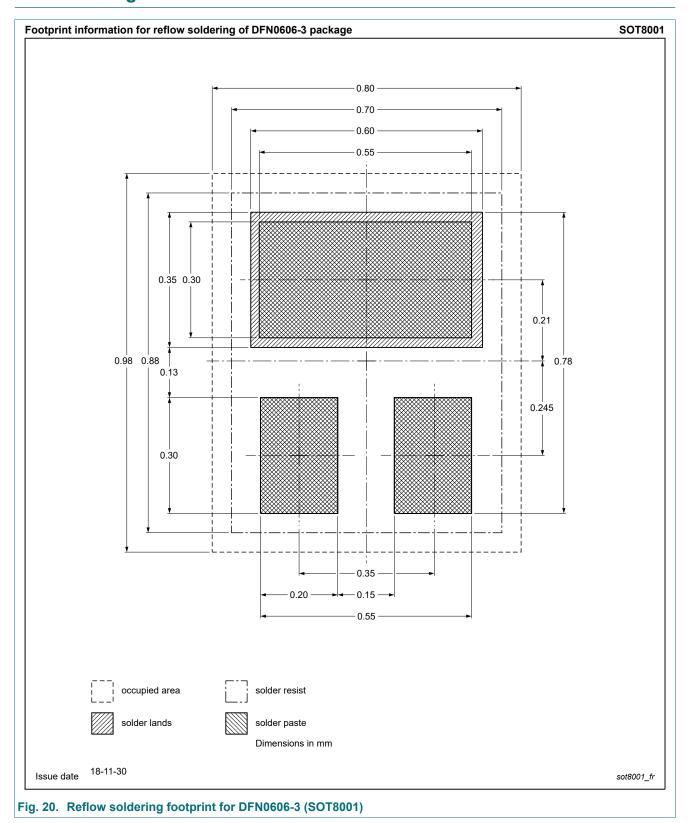
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMH950UPE v.1	20190405	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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